

TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA1937

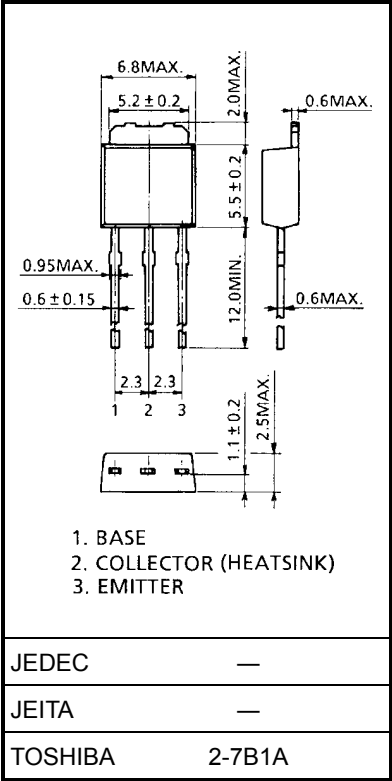
High Voltage Switching Applications

- High voltage: $V_{CEO} = -600\text{ V}$

Maximum Ratings (Ta = 25°C)

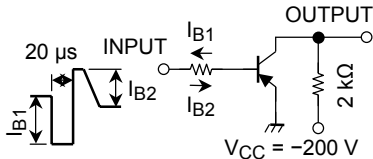
Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	-600	V
Collector-emitter voltage		V_{CEO}	-600	V
Emitter-base voltage		V_{EBO}	-7	V
Collector current	DC	I_C	-0.5	A
	Pulse	I_{CP}	-1	
Base current		I_B	-0.25	A
Collector power dissipation	Ta = 25°C	P_C	1	W
	Tc = 25°C		10	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Unit: mm

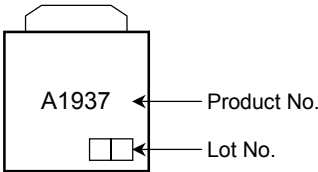


Weight: 0.36 g (typ.)

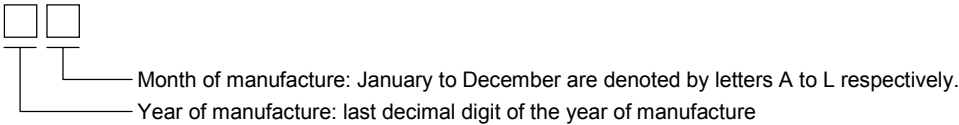
Electrical Characteristics (Ta = 25°C)

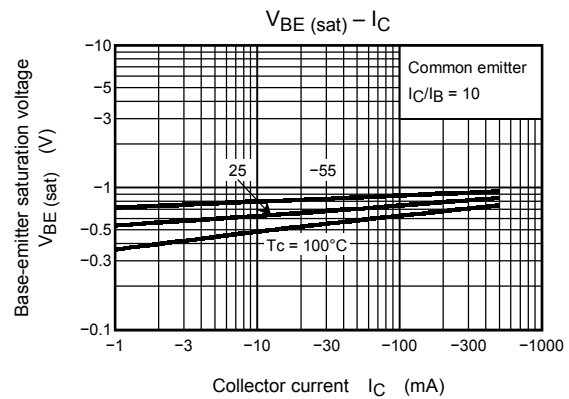
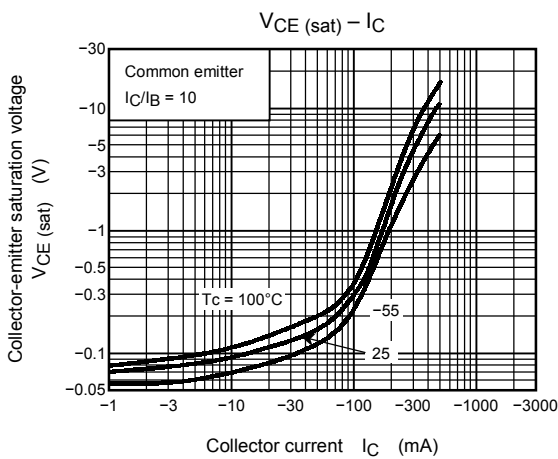
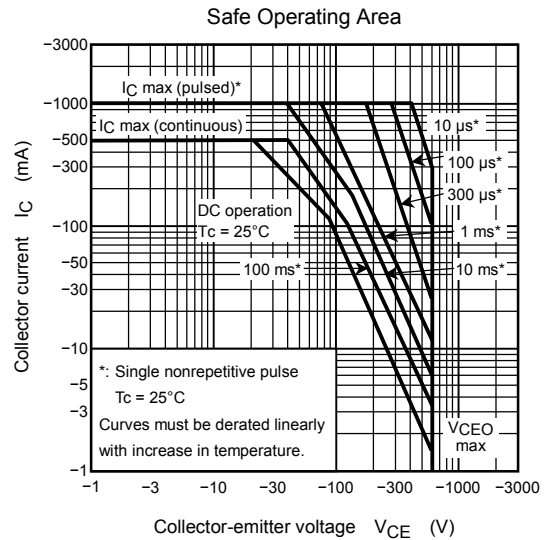
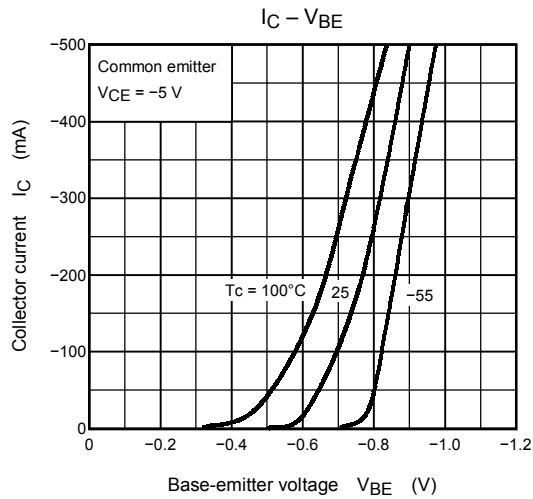
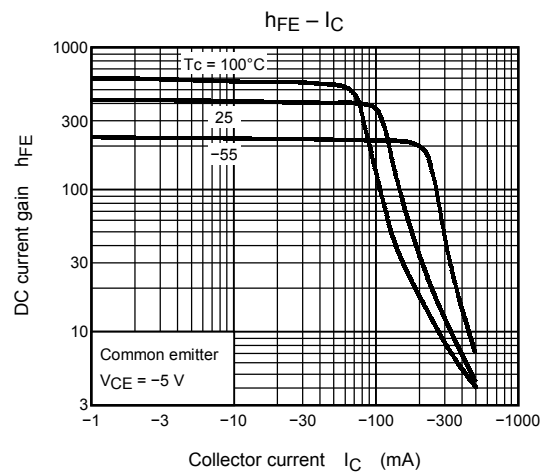
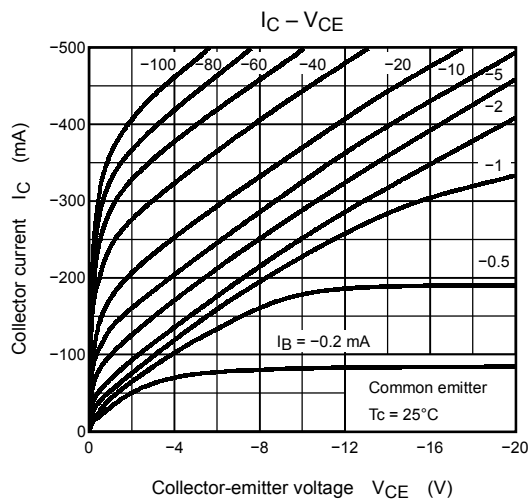
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		ICBO	V _{CB} = -600 V, I _E = 0	—	—	-10	μA
Emitter cut-off current		IEBO	V _{EB} = -7 V, I _C = 0	—	—	-1	μA
Collector-emitter breakdown voltage		V _(BR) CEO	I _C = -10 mA, I _B = 0	-600	—	—	V
DC current gain		h _{FE} (1)	V _{CE} = -5 V, I _C = -20 mA	100	—	500	
		h _{FE} (2)	V _{CE} = -5 V, I _C = -100 mA	80	—	450	
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = -100 mA, I _B = -10 mA	—	—	-1.0	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = -100 mA, I _B = -10 mA	—	-0.76	-0.9	V
Transition frequency		f _T	V _{CE} = -5 V, I _C = -50 mA	—	35	—	MHz
Collector output capacitance		C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	24	—	pF
Switching time	Turn-on time	t _{on}		—	0.2	—	μs
	Storage time	t _{stg}		—	2.3	—	
	Fall time	t _f		—	0.2	—	

Marking



Explanation of Lot No.





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